



60V P-Channel Enhancement Mode MOSFET

Voltage

-60 V

Current

-14 A

Features

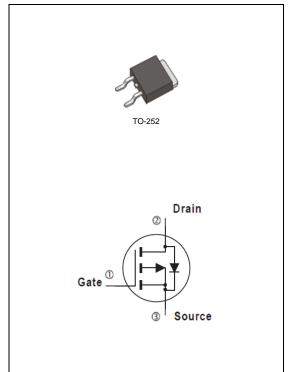
- $R_{DS(ON)}$, $V_{GS}@-10V$, $I_D@-7A<115m\Omega$
- $R_{DS(ON)}$, $V_{GS}@-4.5V$, $I_D@-3.5A<160m\Omega$
- High switching speed
- Improved dv/dt capability
- Low Gate Charge
- Low reverse transfer capacitance
- Acqire quality system certificate: TS16949
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2011/65/EU directive.
- Green molding compound as per IEC61249 Std. (Halogen Free)

Mechanical Data

• Case: TO-252 Package

• Terminals: Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.0104 ounces, 0.297grams



Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS
Drain-Source Voltage		V _{DS}	-60	V
Gate-Source Voltage		V_{GS}	<u>+</u> 20	V
Continuous Drain Current (Note 1)		I_D	-14	Α
Pulsed Drain Current		I _{DM}	-32	Α
Single Pulse Avalanche Energy (Note 2)		E _{AS}	42	mJ
Power Dissipation	T _C =25°C	P _D	45	W
	Derate above 25°C		0.3	W/°C
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55~175	°C
Typical Thermal resistance				
- Junction to Case		$R_{ heta JC}$	3.33	°C/W
- Junction to Ambient (Note 1)		$R_{\theta JA}$	62.5	

• Limited only By Maximum Junction Temperature





Electrical Characteristics (T_A=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS		
Static								
Drain-Source Breakdown Voltage	BV_{DSS}	V _{GS} =0V,I _D =-250uA	-60	-	-	V		
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=-250$ uA	-2.2	-2.76	-3.2	V		
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =-10V,I _D =-7A	-	96	115	mΩ		
Dialii-Source Oil-State Resistance		V _{GS} =-4.5V,I _D =-3.5A	-	125	160			
Zero Gate Voltage Drain Current	I _{DSS}	V_{DS} =-55V, V_{GS} =0V	-	-0.01	-1.0	uA		
Gate-Source Leakage Current	I_{GSS}	V _{GS} = <u>+</u> 20V,V _{DS} =0V	-	<u>+</u> 10	<u>+</u> 100	nA		
Diode Forward Voltage	$V_{\mathtt{SD}}$	I _S =-1A,V _{GS} =0V	-	-0.78	-1.0	V		
Dynamic (Note 5)								
Total Gate Charge	Q_g	V 20V I 42A	-	13.4	-	nC		
Gate-Source Charge	Q_gs	V_{DS} =-30V, I_{D} =-12A, V_{GS} =-10V (Note 2,3)	-	3.4	-			
Gate-Drain Charge	Q_gd	V _{GS} =-10V	-	3.0	-			
Input Capacitance	Ciss	Ciss		685	-			
Output Capacitance	Coss	V_{DS} =-30V, V_{GS} =0V,	-	63	-	pF		
Reverse Transfer Capacitance	Crss	Crss f=1.0MHZ		29	-			
Turn-On Delay Time	td _(on)	d _(on)		7	-			
Turn-On Rise Time	t _r	V_{DS} =-30V,RL=2.5 Ω , V_{GS} =-10V, R _G =6.2 Ω (Note 2,3)	-	40	-	ns		
Turn-Off Delay Time	td _(off)		-	23	-			
Turn-Off Fall Time	t _f		-	10	-			
Drain-Source Diode								
Maximum Continuous Drain-Source					40			
Diode Forward Current	I _S			-	-10	Α		
Reverse Recovery Time	trr	V _{GS} =0V, I _S =-12A	-	28	-	ns		
Reverse Recovery Charge	Qrr	dI _F / dt=-100A/us (Note 2)	-	42	-	nC		

NOTES:

- 1. The test by surface mounted on 1 inch FR4 board with 2oz copper.
- 2. L=0.1mH, I_{AS} =-29A, V_{GS} =-10V, V_{DS} =-25V, R_{G} =25 ohm, Starting T_{J} =25 $^{\circ}$ C
- 3. The Power dissipation is limit by 150°C junction temperature.
- 4. Pulse width<a>300us, Duty cycle<a>2%
- 5. Guaranteed by design, not subject to production testing.





TYPICAL CHARACTERISTIC CURVES

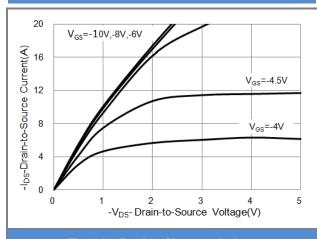


Fig.1 On-Region Characteristics

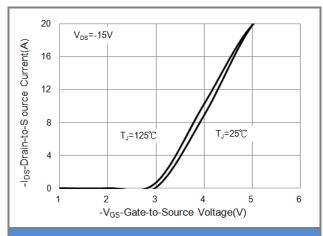


Fig.2 Transfer Characteristics

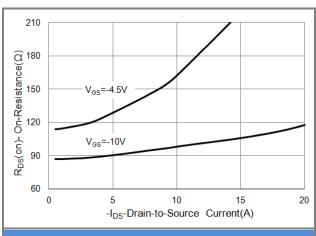


Fig.3 On-Resistance vs. Drain Current

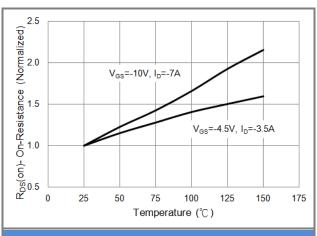


Fig.4 On-Resistance vs. Junction temperature

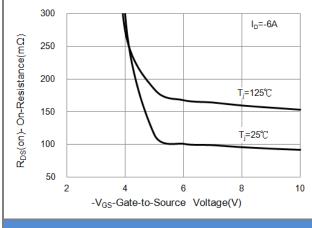


Fig.5 On-Resistance Variation with VGS.

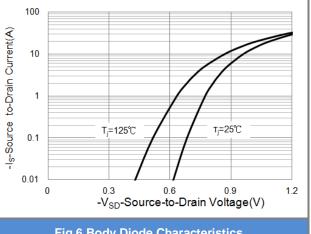


Fig.6 Body Diode Characteristics





TYPICAL CHARACTERISTIC CURVES

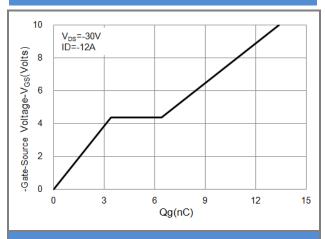


Fig.7 Gate-Charge Characteristics

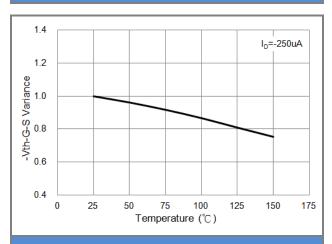
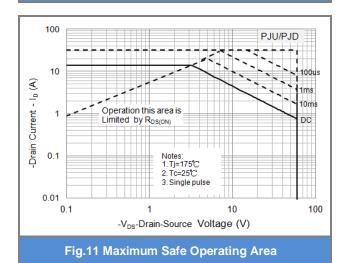


Fig.9 Threshold Voltage Variation with Temperature.



(°C)

1.2

| I_D=-250uA

Fig.8 Breakdown Voltage Variation vs. Temperature

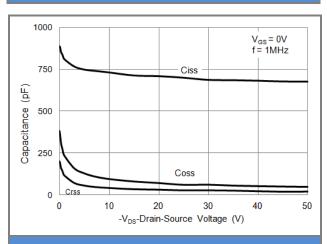


Fig. 10 Capacitance vs. Drain-Source Voltage.





TYPICAL CHARACTERISTIC CURVES

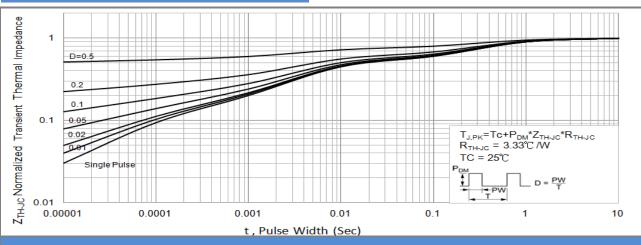
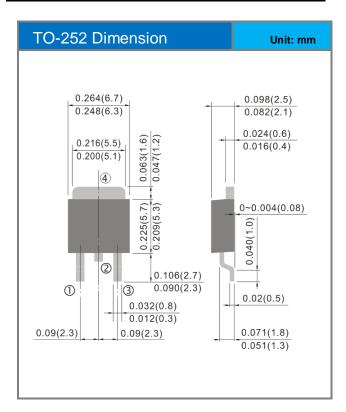


Fig.12 Normalized Thermal Transient Impedance





Packaging Information



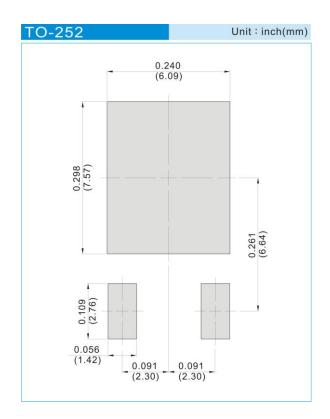




PART NO PACKING CODE VERSION

Part No Packing Code	Package Type	Packing type	Marking	Version	
PJD14P06-AU_L2_000A1	TO-252	3,000pcs / 13" reel	D14P06	Halogen free	

MOUNTING PAD LAYOUT







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